SEMICONDUCTOR

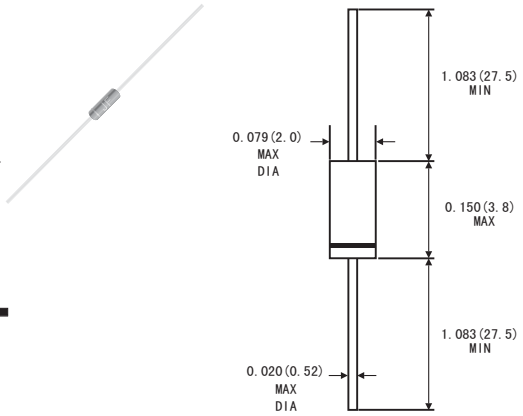
BAT85

SMALL SIGNAL SCHOTTKY DIODES

FEATURES

- For general purpose applications
- These diodes features very low turn-on voltage and fast switching.
  These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.
- This diode is also available in the MiniMELF case with type designation LL85.
- High temperature soldering guaranteed:260°C/10 seconds at terminals
- Component in accordance to RoHS 2011/65/EU

DO-35



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.13 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Repetitive Peak Reverse Voltage	V_R	30	V
Forward Continuous Current at T_A=25°C	I_F	200 [1)]	mA
Repetitive Peak Forward Current at t_p<1s, δ <0.5, T_A=25°C	I_{FM}	300 [1)]	mA
Surge forward current at t_p<10ms , T_A=25°C	I_{FSM}	5 [1)]	A
Power Dissipation at T_A=65°C	P_{tot}	200 [1)]	mW
Junction temperature	T_J	125	°C
Ambient Operating temperature Range	T_A	-55 to+125	°C
Storage Temperature Range	T_{STG}	-55 to+150	°C
1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature			

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Unis
Reverse breakdown voltage Tested with 100μA pulses	$V_{(BR)R}$	30			V
Forward voltage Pulse Test t_p< 300μs,δ< 2% at IF=0.1mA, at IF=1mA, at IF=10mA, at IF=30mA, at IF=100mA	 VF VF VF VF VF		 0.50	 0.24 0.32 0.4 0.8	 V V V V V
Leakage current V_R=25V	I_R			2	μA
Junction Capacitance at V_R=1V ,f=1MHz	C_J			10	pF
Reverse recovery time Form I_F=10mA,I_R=10mA,I_R=1mA	trr			5	ns
Thermal resistance junction to ambient Air	$R_{\theta JA}$			300 [1)]	°C/W
1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature(DO-35)					